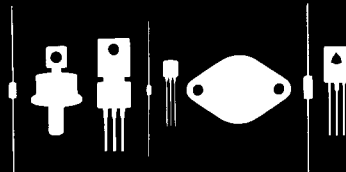


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145 Adams Avenue  
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CQ218I-25B  
CQ218I-25D  
CQ218I-25M  
CQ218I-25N

ISOLATED TAB TRIAC  
25 AMP, 200 THRU 800 VOLTS

TO-218 CASE

## DESCRIPTION

The CENTRAL SEMICONDUCTOR CQ218I-25B series type is an Epoxy Molded Silicon Triac designed for full wave AC control applications featuring gate triggering in all four (4) quadrants. This device is mounted in a TO-218 case with an isolated mounting tab.

## MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise noted)

	SYMBOL	CQ218I -25B	CQ218I -25D	CQ218I -25M	CQ218I -25N	UNITS
Peak Repetitive Off-State Voltage	V <sub>DRM</sub>	200	400	600	800	V
RMS On-State Current (T <sub>C</sub> = 90°C)	I <sub>T(RMS)</sub>			25		A
Peak One Cycle Surge (t = 10ms)	I <sub>TSM</sub>			250		A
I <sup>2</sup> t Value for Fusing (t = 10ms)	I <sup>2</sup> t			312.5		A <sup>2</sup> s
Peak Gate Power (tp = 10μs)	P <sub>GM</sub>			40		W
Average Gate Power Dissipation	P <sub>G(AV)</sub>			1.0		W
Peak Gate Current (tp = 10μs)	I <sub>GM</sub>			10		A
Peak Gate Voltage (tp = 10μs)	V <sub>GM</sub>			16		V
Critical Rate of Rise of On-State Current						
Repetitive (F = 50Hz)	di/dt			10		A/μs
Storage Temperature	T <sub>stg</sub>		-40 to +150			°C
Junction Temperature	T <sub>J</sub>		-40 to +125			°C
Thermal Resistance	θ <sub>J-A</sub>			50		°C/W
Thermal Resistance	θ <sub>J-C</sub>			1.5		°C/W
Isolation Voltage	V <sub>ISO</sub>			2500		V(RMS)

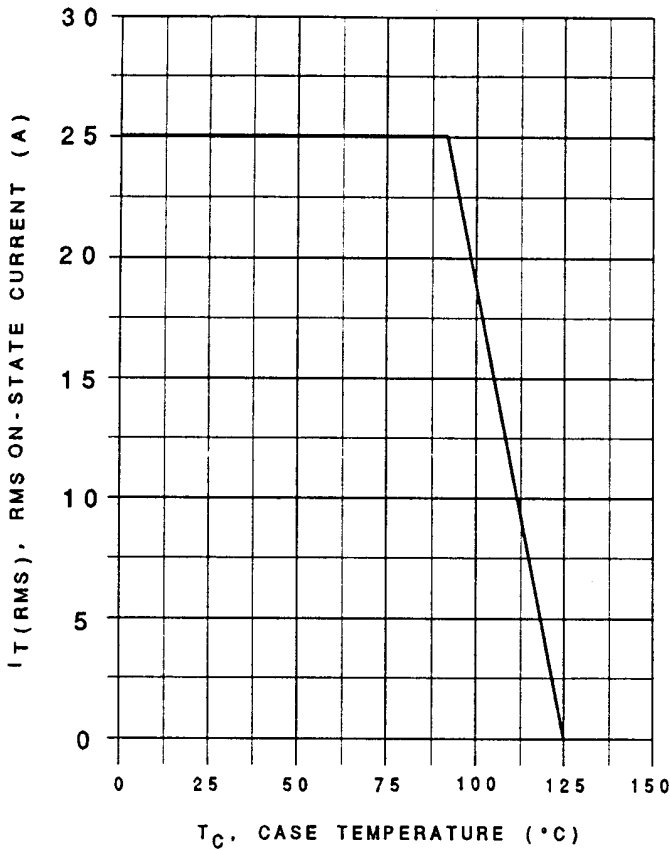
## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I <sub>DRM</sub>	Rated V <sub>DRM</sub>			0.01	mA
I <sub>DRM</sub>	Rated V <sub>DRM</sub> , T <sub>C</sub> = 125°C			6.00	mA
I <sub>GT</sub>	V <sub>D</sub> = 12V, R <sub>L</sub> = 33Ω, QUAD I,II,III			50	mA
I <sub>GT</sub>	V <sub>D</sub> = 12V, R <sub>L</sub> = 33Ω, QUAD IV			100	mA
I <sub>H</sub>	I <sub>T</sub> = 500mA			80	mA
V <sub>GT</sub>	V <sub>D</sub> = 12V, R <sub>L</sub> = 33Ω, QUAD I,II,III,IV			1.50	V
V <sub>TM</sub>	I <sub>TM</sub> = 35A, tp = 10ms			1.70	V
dv/dt	V <sub>D</sub> = 2/3 V <sub>DRM</sub> , R <sub>GK</sub> = ∞, T <sub>C</sub> = 125°C	250			V/μs

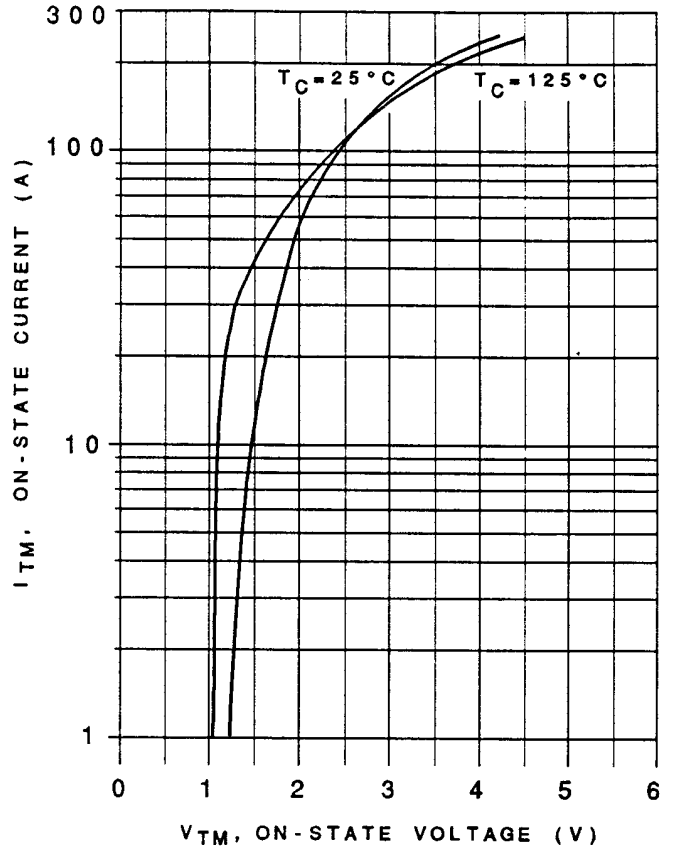
(OVER)

# CQ218I-25B SERIES RATING AND CHARACTERISTIC CURVES

RMS ON-STATE CURRENT vs. CASE TEMPERATURE



MAXIMUM ON-STATE CHARACTERISTICS



## MECHANICAL OUTLINE

ALL DIMENSIONS IN INCHES (mm).

